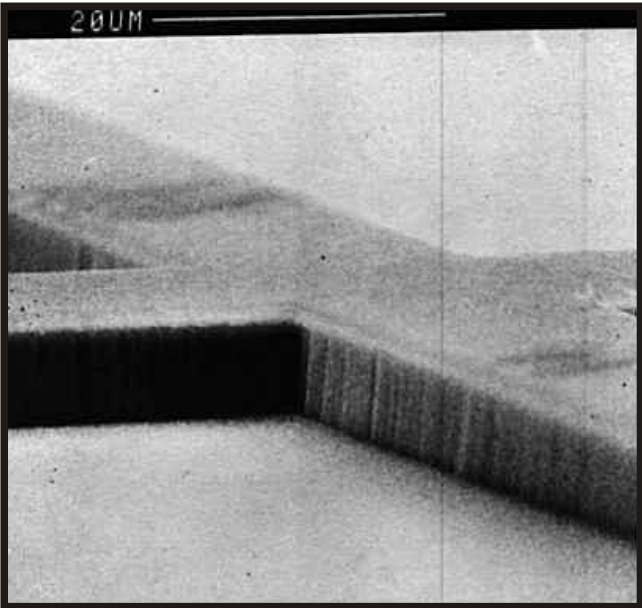


Plasmalab Data

RIE of Waveguides in InP



7 and 3 µm deep, anisotropic etches in InP

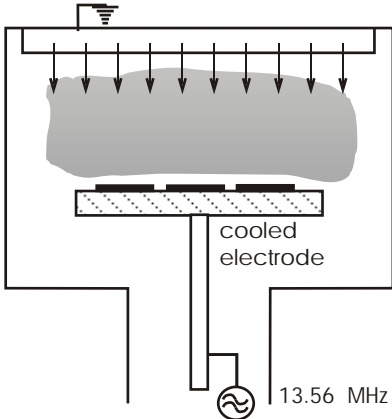
Plasmalab 80 Plus



Plasmalab System 100

Plasmalab System 133

Technology:
Parallel Plate Reactor
Shower Head Gas Inlet
13.56 MHz Plasma Excitation
Process:
CH₄ / H₂b used at room temperature
(CH₄ / H₂/ Cl₂ based at ca. 200 °C can be used at 100 - 200 nm/ min.)



Results:
Rate :
InP 30 - 60 nm/ min
InGaAs 20-40 nm/ min
GaAs 10-20 nm/ min
uniformity ±3% across 2" wafer
±5% across table
profile > 85°
surface roughness < 3 nm RMS
mask selectivities:
InP:SiO₂>15:1
InP:SiN_x>15:1
InP:resist>5:1